

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: JAMES D. PARSONS

Title: ACOUSTIC ABSORPTION RADIATION SENSING IN SiC

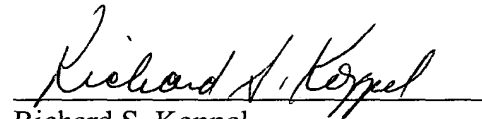
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

TRANSMITTAL FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is an Information Disclosure Statement for the above application. We authorize the Commissioner to charge payment of any additional fees required in connection with this application to Deposit Account No. 11-1580. We enclose a copy of this sheet.

Respectfully submitted,



Richard S. Koppel
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Attorney for Applicant

September 5, 2003

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INFORMATION DISCLOSURE STATEMENT

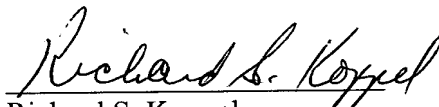
Sir:

Enclosed are Form PTO-1449 and copies of the listed non-U.S. patent references for the above application.

The filing of this information disclosure statement shall not be construed as a representation that a search has been made (37 C.F.R. 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The filing of this information disclosure statement shall not be construed as an admission against interest in any manner. Notice of January 9, 1992, 1135 O.G. 13-25, at 25.

Respectfully submitted,



Richard S. Koppel
Registration No. 26,475
Attorney for Applicant

September 5, 2003

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FORM PTO-1449 (Modified) INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Docket No. 378-21-034	Application Number
	Applicant James D. Parsons	
	Filing Date	Group Art Unit

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number							Date	Name	Class	Subclass	Filing Date If Appropriate
	6	2	3	9	4	3	2	05-2001	Parsons	250	338.1	
	5	1	2	2	6	6	8	06-1992	Kajiwara et al.	338	18	
	5	8	6	8	4	9	7A	02-1999	Jung	374	179	
	5	0	2	5	2	4	3A	06-1991	Ichikawa	338	19	
	4	6	9	5	7	3	3A	09-1987	Pesavento	250	551	

FOREIGN PATENT DOCUMENTS

	Document Number							Date	Country	Class	Subclass	Translation	
												Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1.	DE VASCONCELOS E A ET AL: "Highly sensitive thermistors based on high-purity polycrystalline cubic silicon carbide" SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, Vol. 83, no. 1-3, May 2000 (2000-05), pages 167-171, XP004198310 ISSN: 0924-4247
	2	DE VASCONCELOS E A ET AL: "Potential of high-purity polycrystalline silicon carbide for thermistor applications" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 1 (REGULAR PAPERS, SHORT NOTES & REVIEW PAPERS), SEPT. 1998, PUBLICATION OFFICE, JAPANESE JOURNAL APPL. PHYS, JAPAN, vol. 37, no. 9A, pages 5078-5079, XP002211060 ISSN: 0021-4922
	3	Materials for High Temperature Semiconductor Devices: Committee on Materials for High-Temperature Semiconductor Devices, National Materials Advisory Board, Commission on Engineering and Technical Systems, National Research Council: National Academy Press, Washington, D.C., 1995, pp.68-70.
	4	O. Nennewitz, L. Spiess and V. Breternitz, "Ohmic Contacts to 6H-SiC", Applied Surface Science, Vol. 91, 1995, pages 347-351.
	5	J.A. Lely and F.A. Kroeger, "Electrical Properties of Hexagonal SiC Doped with N, B or Al", In Semiconductors and Phosphors, Proceedings of Intl. Colloquium-Partenkirchen, Ed. M. Schoen and H. Welker, New York, Interscience Pub., Inc. 1958, pp. 525-533.
	6	Q.Y. Tong, U. Gosele, C. Yuan, A.J. Stecki & M. Reiche, "Silicon Carbide Wafer Bonding", J. Electrochem Soc., Vol. 142, No. 1, January 1995, pp. 232-236.
Examiner		Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (Modified)

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket No. 378-21-034

Application Number

Applicant James D. Parsons

Filing Date

Group Art Unit

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	13	Takashi Nagel and Masahiko Itch, "Sic Thin-Film Thermistors", IEEE Transactions on Industry Applications, Vol. 26, No. 6, November/December 1990, pp. 1139-1143.1
	14	"Electrical Properties of β -Sic Heavily Doped with Nitrogen" O. A. Golikova, L.M. Ivanova, A. A. Pletyushiin, and V.P. Semenenko, A.A. Balkov Institute of Metallurgy, Academy of Sciences of the USSR, Moscow Institute of Semiconductors, Academy of Sciences of the USSR, Leningrad Translated from Fizika I Tehnika Poluprovodnikov, Vol. 5, No. 3, pp. 417-420, March 1971, Original article submitted May 26, 1970; revision submitted July 8, 1970.
	15	"Galvanomagnetic Effects in n-type Silicon Carbide at Low Temperatures", M.I. Iglitsyn, M. Mirzabaev, V.M. Tuchkevich, E.F. Fedomova, and Yu. V. Shmartsev, A.F. Ioffe Physicotechnical Institute, Academy of Sciences, USSR, Leningrad State Research and Planning Institute for the Rare Metal Industry, Moscow, Translated from fizika Tverdogo Tela, Vol. 6, No. 9, pp. 2673-2682, September, 1964, Originak article submitted March 31, 1964

Examiner	Date Considered
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